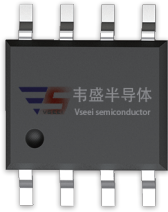
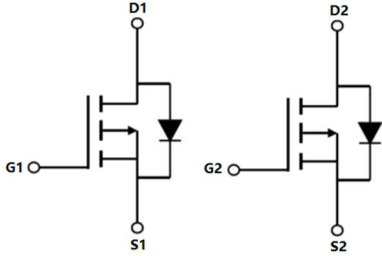


Description

Features <ul style="list-style-type: none"> ● $V_{DS} = -30V$, $I_D = -11A$ $R_{DS(ON)} < 16.5m\Omega$ @ $V_{GS} = -10V$ $R_{DS(ON)} < 26.5m\Omega$ @ $V_{GS} = -4.5V$ ● Advanced Trench Technology ● Excellent $R_{DS(ON)}$ and Low Gate Charge ● Lead free product is acquired 	Application <ul style="list-style-type: none"> ● PWM Applications ● Load Switch ● Power Management <p>100% UIS 100% ΔV_{ds}</p>
 SOP-8	 Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
VSM11DP03-S8	VSM11DP03	TAPING	SOP-8	13inch	4000	48000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	-11	A
		$T_A = 100^\circ C$	-7	A
I_{DM}	Pulsed Drain Current ^{note1}		-44	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		68	mJ
P_D	Power Dissipation	$T_A = 25^\circ C$	3.6	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		34.7	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ C$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} = -10V, I _D = -10A	-	12.7	16.5	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	19	26.5	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	2130	-	pF
C _{oss}	Output Capacitance		-	280	-	pF
C _{rss}	Reverse Transfer Capacitance		-	252	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -5A, V _{GS} = -10V	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	4	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	5.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -10A, V _{GS} = -10V, R _{GEN} =2.5Ω	-	9	-	ns
t _r	Turn-on Rise Time		-	13	-	ns
t _{d(off)}	Turn-off Delay Time		-	48	-	ns
t _f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-11	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-44	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -11A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. E_{AS} condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=-15V$, $V_G=-10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=-16.5A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

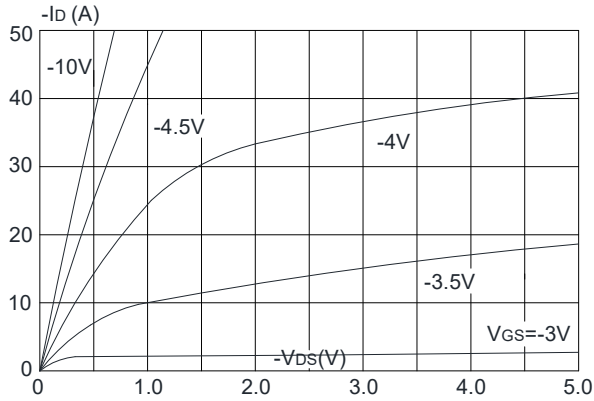
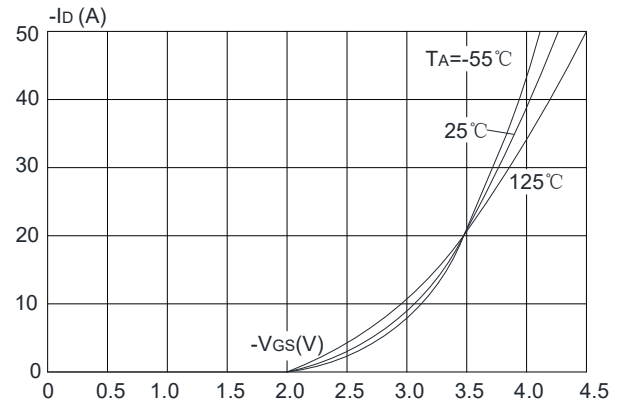
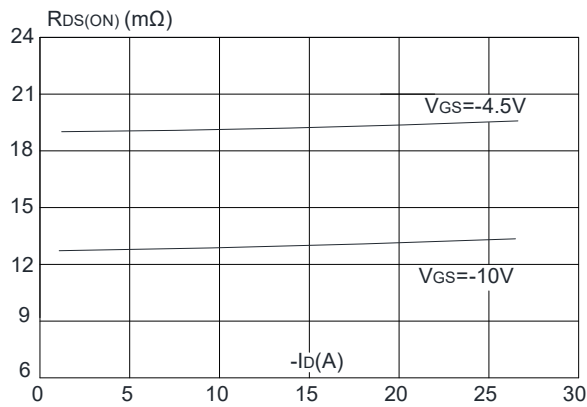
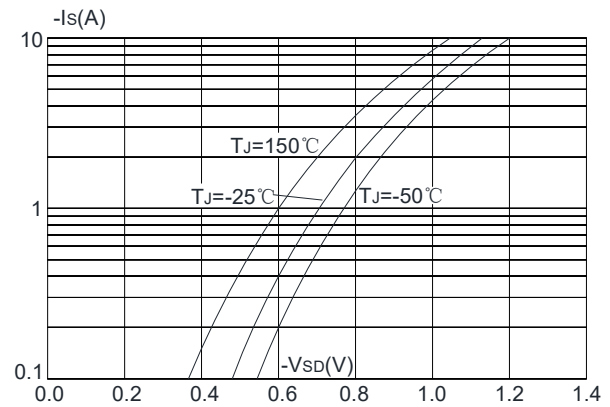
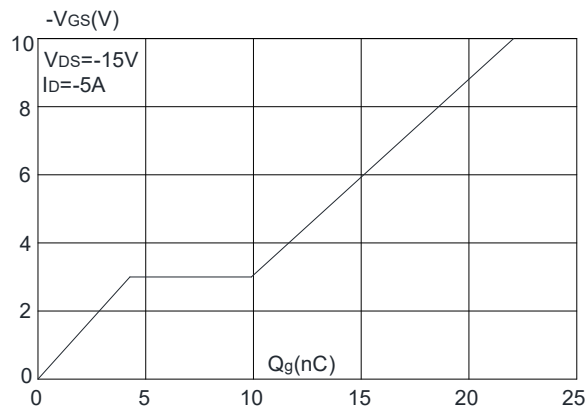
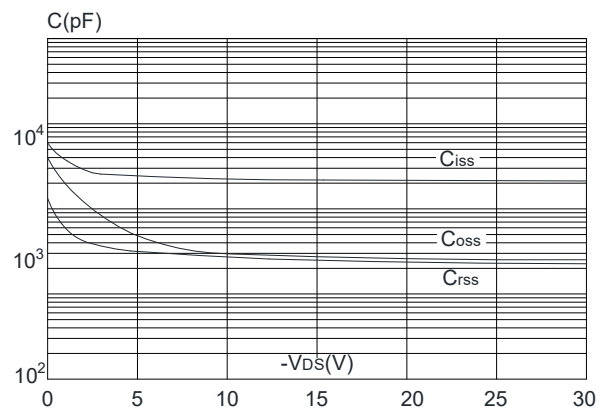
Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

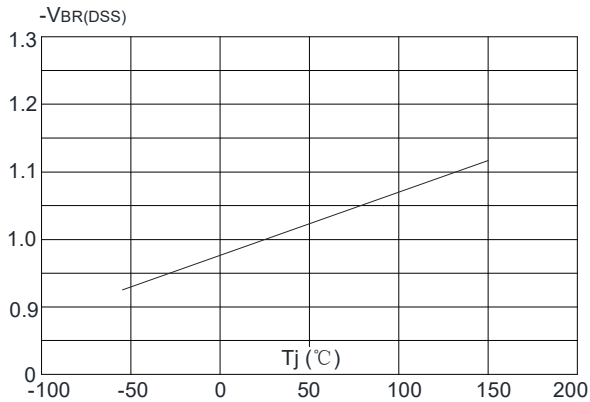


Figure 8: Normalized on Resistance vs. Junction Temperature

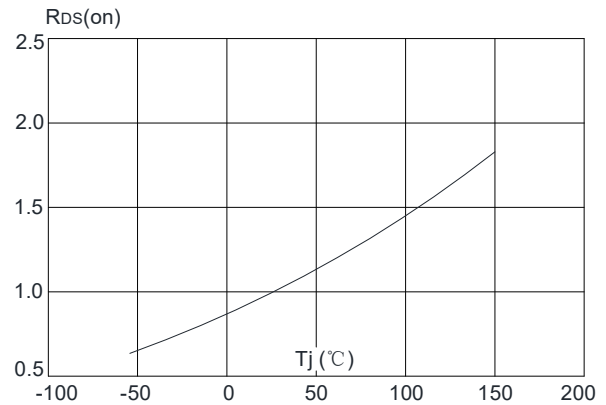


Figure 9: Maximum Safe Operating Area

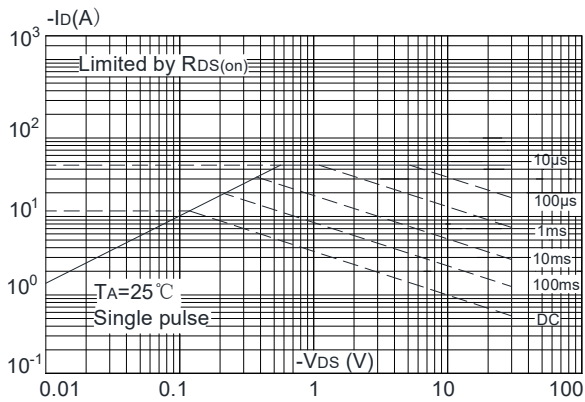


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

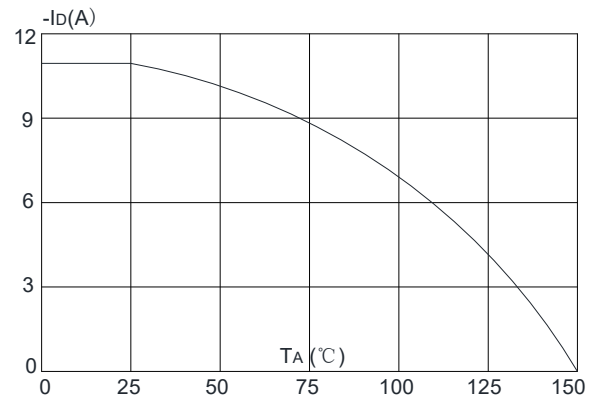
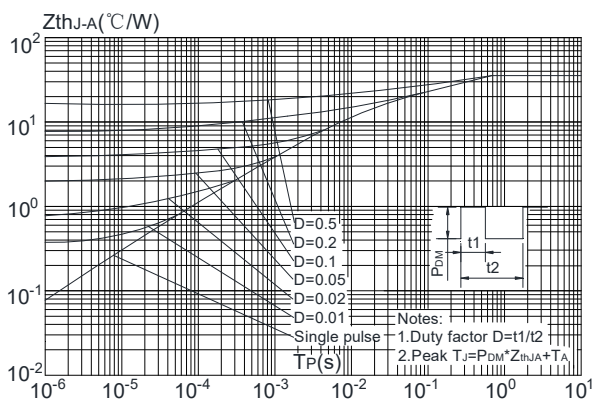
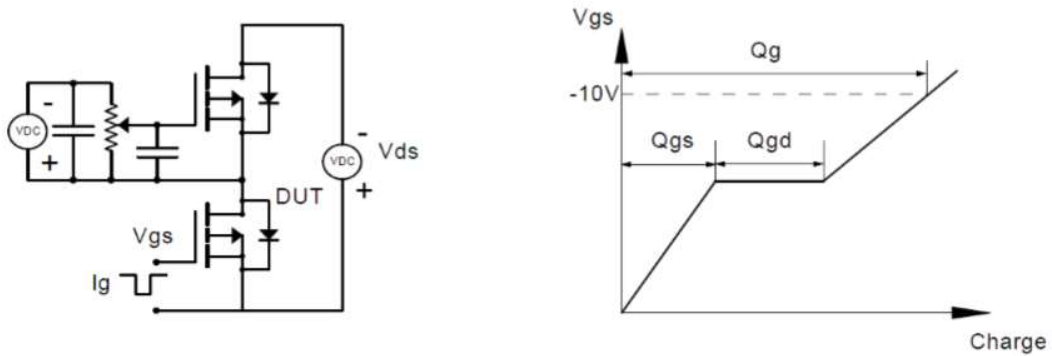


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

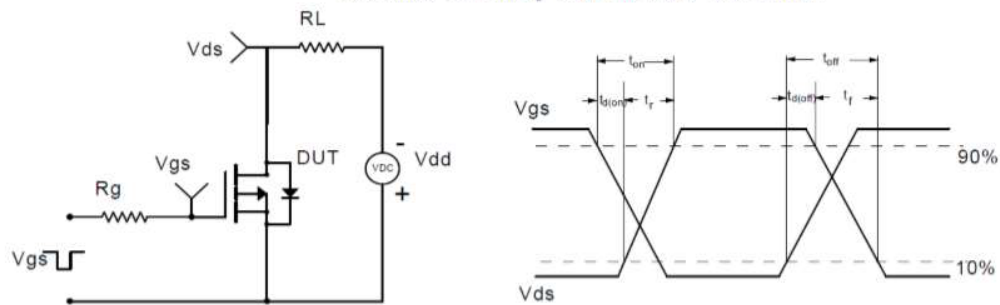


Test Circuit

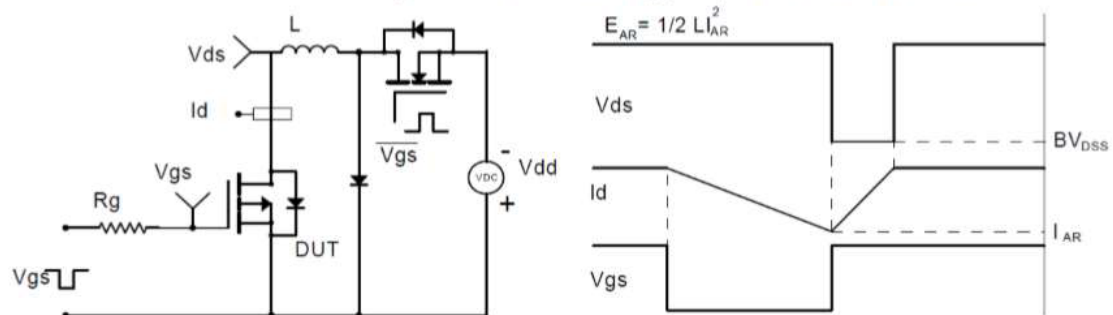
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

